

## ABSTRACT

A semiconductor device has interconnecting lines disposed side by side in a dielectric film. Mutually adjacent pairs of interconnecting lines are separated by a substantially constant distance from top to bottom, but the width of each interconnecting line varies from top to bottom. For example, the interconnecting lines may have T-shaped or trapezoidal cross sections, interconnecting lines having wide tops alternating with interconnecting lines having wide bottoms. These cross-sectional shapes can be formed by simple fabrication processes. Since the facing sides of mutually adjacent interconnecting lines do not form mutually parallel vertical planes and therefore do not function as parallel plate electrodes, the interconnect capacitance is reduced.